

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	354956	438/\$.ccls. 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	114923	1 and (transistor or MOS or MOSFET or CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	16	2 and (densify\$3 or densificattion) near (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	3	3 and (non-oxidizing near (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	3	4 and (silicide or polycide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	10	(lowe-brett-d or smythe-john-a or carns-timothy-k).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	3	6 and (densify\$3 or densificattion) near (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	1	((densify\$3 or densificattion) near (spacer or sidewall)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	26	(densify\$3 or densificattion) near (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	20	9 and (transistor or MOS or MOSFET or CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	4	10 and (non-oxidizing near (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	